

## PNP Silicon Epitaxial Transistor

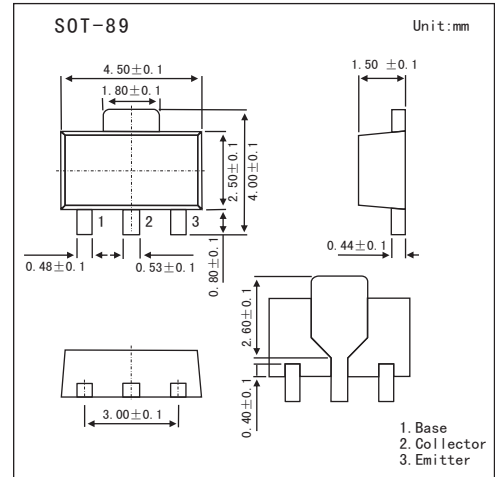
### KTA1273

#### Features

Collector Power Dissipation:  $P_c=500\text{mW}$

Collector current:  $I_c=-2\text{A}$

Complementary to KTC3205



#### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-30	V
Collector to emitter voltage	$V_{CEO}$	-30	V
Emitter to base voltage	$V_{EBO}$	-5	V
Collector current (DC)	$I_c$	-2	A
Collector Power Dissipation	$P_c$	500	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

#### Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-1\text{mA}, I_E=0$	-30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_c=0$	-5			V
Collector cutoff current	$I_{CBO}$	$V_{CB}=-30\text{V}, I_E=0\text{A}$			-0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_c=0\text{A}$			-0.1	$\mu\text{A}$
DC current gain *	$h_{FE}$	$V_{CE}=-2\text{V}, I_c=-500\text{mA}$	100		320	
Collector saturation voltage	$V_{CE(sat)}$	$I_c=-1.5\text{A}, I_B=-30\text{mA}$			-2	V
Base to emitter voltage	$V_{BE}$	$V_{CE}=-2\text{V}, I_c=-500\text{mA}$			-1	V
Transition frequency	$f_T$	$V_{CE}=-2\text{V}, I_E=500\text{mA}$		120		MHz
Output capacitance	$C_{ob}$	$V_{CE}=-10\text{V}, I_E=0, f=1.0\text{MHz}$		48		pF

\* Pulsed: PW 350  $\mu\text{s}$ , Duty Cycle 2%

#### $h_{FE}$ Classification

Rank	O	Y
Range	100 200	160 320